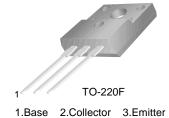


FJPF5027

High Voltage and High Reliability

- High Speed Switching
- Wide SOA



NPN Silicon Transistor

Absolute Maximum Ratings T_C=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	1100	V
V _{CEO}	Collector-Emitter Voltage	800	V
V _{EBO}	Emitter-Base Voltage	7	V
I _C	Collector Current (DC)	3	А
I _{CP}	Collector Current (Pulse)	10	А
I _B	Base Current	1.5	Α
P _C	Collector Dissipation (T _C =25°C)	40	W
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	- 55 ~ 150	°C

Electrical Characteristics $T_C=25$ °C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage	$I_{C} = 1 \text{mA}, I_{E} = 0$	1100			V
BV _{CEO}	Collector-Emitter Breakdown Voltage	$I_{C} = 5mA, I_{B} = 0$	800			V
BV _{EBO}	Emitter-Base Breakdown Voltage	$I_E = 1 \text{mA}, I_C = 0$	7			V
V _{CEX} (sus)	Collector-Emitter Sustaining Voltage	$I_C = 1.5A$, $I_{B1} = -I_{B2} = 0.3A$ L = 2mH, Clamped	800			V
I _{CBO}	Collector Cut-off Current	$V_{CB} = 800 \text{V}, I_{E} = 0$			10	μΑ
I _{EBO}	Emitter Cut-off Current	$V_{EB} = 5V, I_{C} = 0$			10	μΑ
h _{FE1}	DC Current Gain	$V_{CE} = 5V, I_{C} = 0.2A$	10		40	
h _{FE2}		$V_{CE} = 5V, I_{C} = 1A$	8			
V _{CE} (sat)	Collector-Emitter Saturation Voltage	$I_C = 1.5A, I_B = 0.3A$			2	V
V _{BE} (sat)	Base-Emitter Saturation Voltage	$I_C = 1.5A, I_B = 0.3A$			1.5	V
C _{ob}	Output Capacitance	$V_{CB} = 10V, I_{E} = 0, f = 1MHz$		60		pF
f _T	Current Gain Bandwidth Product	$V_{CE} = 10V, I_{C} = 0.2A$		15		MHz
t _{ON}	Turn On Time	V _{CC} = 400V			0.5	μs
t _{STG}	Storage Time	$I_C = 5I_{B1} = -2.5I_{B2} = 2A$			3	μs
t _F	Fall Time	$R_L = 200\Omega$			0.3	μs

h_{FE} Classification

Classification	N	R	0
h _{FE1}	10 ~ 20	15 ~ 30	20 ~ 40

Typical Characteristics

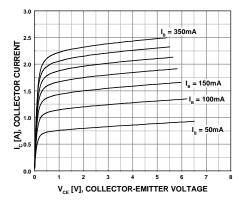


Figure 1. Static Characteristic

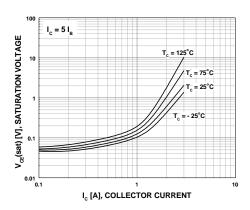


Figure 3. Saturation Voltage

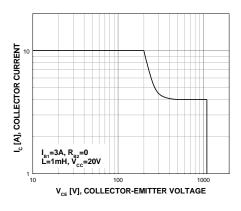


Figure 5. Reverse Bias Safe Operating Area

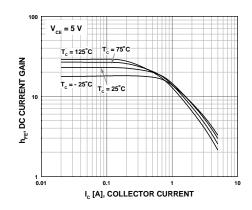


Figure 2. DC current Gain

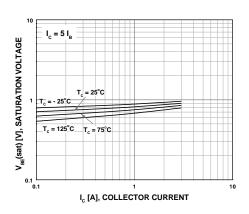


Figure 4. Saturation Voltage

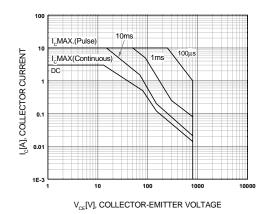
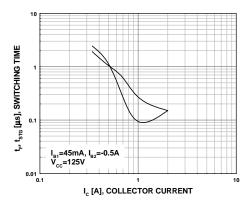


Figure 6. Forward Bias Safe Operating Area

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Typical Characteristics (Continued)



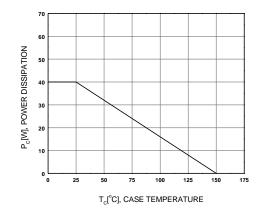
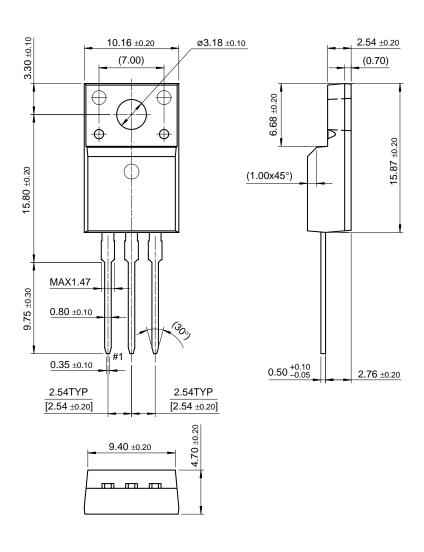


Figure 7. Resistive Load Switching Characteristics

Figure 8. Power Derating

Package Dimensions

TO-220F



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FACT™	ISOPLANAR™	OPTOLOGIC [®]	SMART START™	VCX^{TM}
Across the board.	Around the world.™	OPTOPLANAR™	SPM™	
The Power Franchise™		PACMAN™	Stealth™	
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